

<b>SPEC SHEET (FOR REFERENCE)</b>	SHEET No.	<b>G05052A</b>	Page.
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TYPE : 6PT2003N3T\*\*

CHIP SIZE	0.23 * 0.23 mm
WAFER SIZE	6 inch
POSSIBLE DIE PER WAFER	290,000 pcs

Maximum Ratings(Ta=25°C)

Characteristics	Symbol	Ratings	Unit
Drain-source voltage	VDSS	30	V
Gate-source voltage	VGSS	±20	V
Drain Current (DC)	ID	0.15	A

\* For Reference

WAFER PROBING SPEC (Ta=25°C)

No	MODE	LIMIT				CONDITIONS
		MIN.	Typ	MAX.	UNIT	
1	IGSS			±5	uA	VGS=±20V VDS=0V
2	IDSS			1	uA	VDS=30V VGS=0V
3	BVDSS	32			V	ID=100uA
4	Vgs(off)	0.7		1.5	V	ID=100uA VDS=3.0V
5	Ron 1		3	5	Ω	ID=10mA VGS=4.0V
6	Ron 2		5.5	9.0	Ω	ID=1mA VGS=2.5V
7	VSD			1	V	IS=10mA

※ Built-in ZD between Gate and Source.  
ESD Protected (350V typ)

TENTATIVE

NOTE: